

Parameter	Tr1 and Tr2
$V_{CEO}$	20V
$V_{EBO}$	12V
I <sub>C</sub>	600mA
R <sub>1</sub>	10kΩ

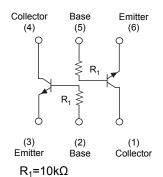
# Outline SMT6 (3) (2) (1)

SOT-457 (SC-74)

#### Features

- 1) Built-In Biasing Resistors
- 2) Two DTC614T chips in one package.
- 3) Low saturation voltage, typically  $V_{CE(sat)}$  =40mV at  $I_C$  /  $I_B$ =50mA / 2.5mA, makes these transistors ideal for muting circuits.
- 4) These transistors can be used at high current levels,  $I_{\rm C}$ =600mA.
- 5) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 6) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 7) Lead Free/RoHS Compliant.

## •Inner circuit



#### Application

Muting circuit

#### Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
IMH21	SMT6	2928	T110	180	8	3,000	H21

# ●Absolute maximum ratings (Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Values	Unit
Collector-base voltage	V <sub>CBO</sub> 20		V
Collector-emitter voltage	ige V <sub>CEO</sub>		V
Emitter-base voltage	$V_{EBO}$	12	V
Callegator augment	I <sub>C</sub>	600	mA
Collector current	I <sub>CP</sub> *1	1	Α
Power dissipation	P <sub>D</sub> *2	300(Total) *3	mW
Junction temperature	T <sub>j</sub>	150	°C
Range of storage temperature	T <sub>stg</sub>	−55 to +150	°C

### ●Electrical characteristics (Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV <sub>CBO</sub>	I <sub>C</sub> = 50μA	20	-	-	V
Collector-emitter breakdown voltage	BV <sub>CEO</sub>	I <sub>C</sub> = 1mA	20	-	-	V
Emitter-base breakdown voltage	BV <sub>EBO</sub>	I <sub>E</sub> = 50μA	12	-	-	V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 20V	-	1	0.5	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 12V	ı	ı	0.5	μΑ
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C}$ / $I_{\rm B}$ = 50mA / 2.5mA	ı	40	150	mV
DC current gain	h <sub>FE</sub>	$V_{CE}$ = 5V, $I_{C}$ = 50mA	820	-	2700	-
Input resistance	R <sub>1</sub>	-	7	10	13	kΩ
Transition frequency	f <sub>T</sub> *4	$V_{CE} = 10V, I_{E} = -50mA$ f = 100MHz	-	150	-	MHz
Output ON Resistance	R <sub>on</sub>	$V_1 = 5V$ $R_L = 1k\Omega, f = 1kHz$	-	0.9	-	Ω

<sup>\*1</sup> P<sub>W</sub>=10ms, Single pulse

<sup>\*2</sup> Each terminal mounted on a reference footprint

<sup>\*3 200</sup>mW per element must not be exceeded.

<sup>\*4</sup> Characteristics of built-in transistor

#### ●Electrical characteristic curves(Ta = 25°C)

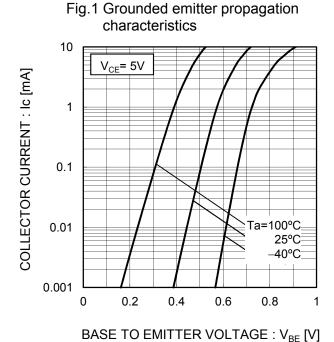


Fig.2 Grounded emitter output characteristics 0.9mA 600 0.8mA Ta=25°C 0.7mA 0.6mA 0.5mA 400 0.4mA 0.3mA 0.2mA 200 0.1mA 0 0A 2 10

COLLECTOR CURRENT : I<sub>C</sub> [mA]

COLLECTOR TO EMITTER VOLTAGE :  $V_{CE}[V]$ 

Fig.4 Collector-emitter saturation voltage

Fig.3 DC Current gain vs. Collector Current

10000

VcE=5V

Ta=100°C

25°C

40°C

-40°C

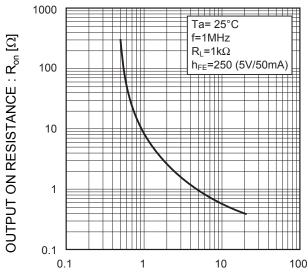
COLLECTOR CURRENT: I<sub>C</sub> [mA]

vs. Collector Current 10000  $I_C/I_B=20$ COLLECTOR SATURATION VOLTAGE: V<sub>CE(sat)</sub> [mV] 1000 100 Ta= 100°C 25°C 40°C 10 0.1 10 100 1000 COLLECTOR CURRENT : I<sub>C</sub> [mA]

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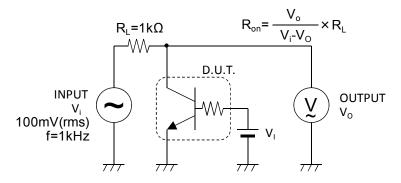
# ●Electrical characteristic curves(Ta = 25°C)

Fig.5 Output ON resistance vs. input voltage

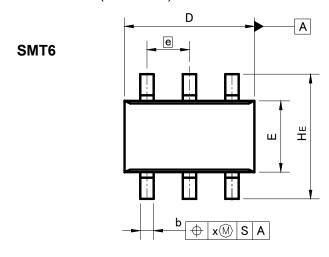


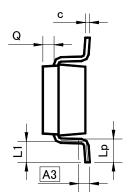
INPUT VOLTAGE: V<sub>I</sub> [V]

Fig.6 Ron measurement circuit.

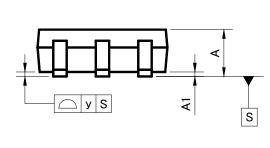


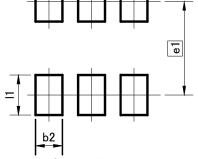
# ●Dimensions (Unit : mm)





е





Pattern of terminal position areas [Not a recommended pattern of soldering pads]

DIM	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.00	1.30	0.039	0.051	
A1	0.00	0.10	0.000	0.004	
A3	0.5	25	0.010		
b	0.25	0.40	0.010	0.016	
С	0.09	0.25	0.004	0.010	
D	2.80	3.00	0.110	0.118	
Е	E 1.50	1.80	0.059	0.071	
е	0.9	95	0.0	37	
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.20	0.30	0.008	0.012	
х	_	0.20		0.008	
У	_	0.10	_	0.004	

DIM	MILIMETERS		INCHES		
	DIM	MIN	MAX	MIN	MAX
	b2		0.60	ı	0.024
	e1	2.	10	0.0	83
	11	ı	0.90	ı	0.035

Dimension in mm / inches

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